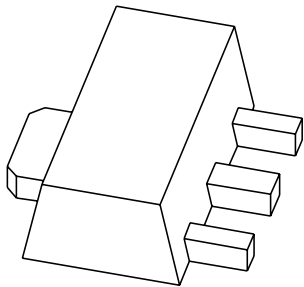


# DATA SHEET



## **BST50; BST51; BST52** NPN Darlington transistors

Product data sheet  
Supersedes data of 2001 Feb 20

2004 Dec 09

# NPN Darlington transistors

# BST50; BST51; BST52

### FEATURES

- High current (max. 0.5 A)
- Low voltage (max. 80 V)
- Integrated diode and resistor.

### APPLICATIONS

- Industrial switching applications such as:
  - Print hammer
  - Solenoid
  - Relay and lamp driving.

### DESCRIPTION

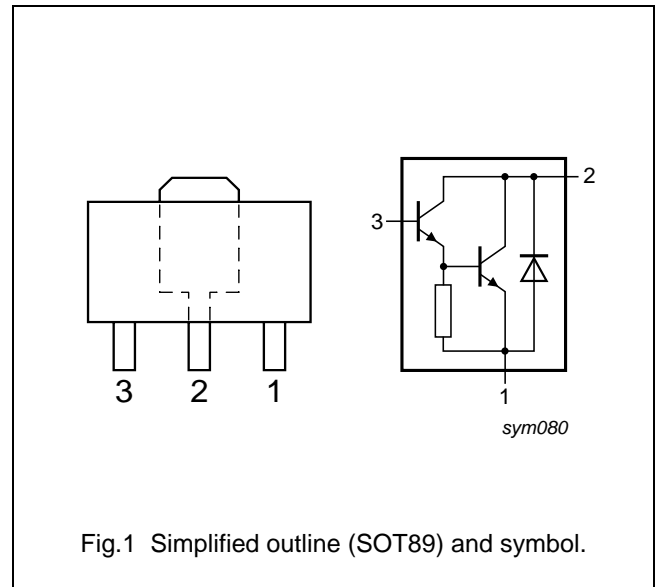
NPN Darlington transistor in a SOT89 plastic package.  
PNP complements: BST60, BST61 and BST62.

### MARKING

TYPE NUMBER	MARKING CODE
BST50	AS1
BST51	AS2
BST52	AS3

### PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BST50	SC-62	plastic surface mounted package; collector pad for good heat transfer; 3 leads	SOT89
BST51			
BST52			

## NPN Darlington transistors

## BST50; BST51; BST52

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BST50		–	60	V
	BST51		–	80	V
	BST52		–	90	V
V <sub>CES</sub>	collector-emitter voltage	V <sub>BE</sub> = 0 V			
	BST50		–	45	V
	BST51		–	60	V
	BST52		–	80	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	5	V
I <sub>C</sub>	collector current (DC)		–	1	A
I <sub>CM</sub>	peak collector current		–	2	A
I <sub>B</sub>	base current (DC)		–	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	–	1.3	W
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	ambient temperature		–65	+150	°C
T <sub>stg</sub>	storage temperature		–65	+150	°C

**Note**

- Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.  
For other mounting conditions, see “*Thermal considerations for SOT89 in the General Part of associated Handbook*”.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	96	K/W
R <sub>th(j-s)</sub>	thermal resistance from junction to soldering point		16	K/W

**Note**

- Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.  
For other mounting conditions, see “*Thermal considerations for SOT89 in the General Part of associated Handbook*”.

## NPN Darlington transistors

## BST50; BST51; BST52

**CHARACTERISTICS**

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

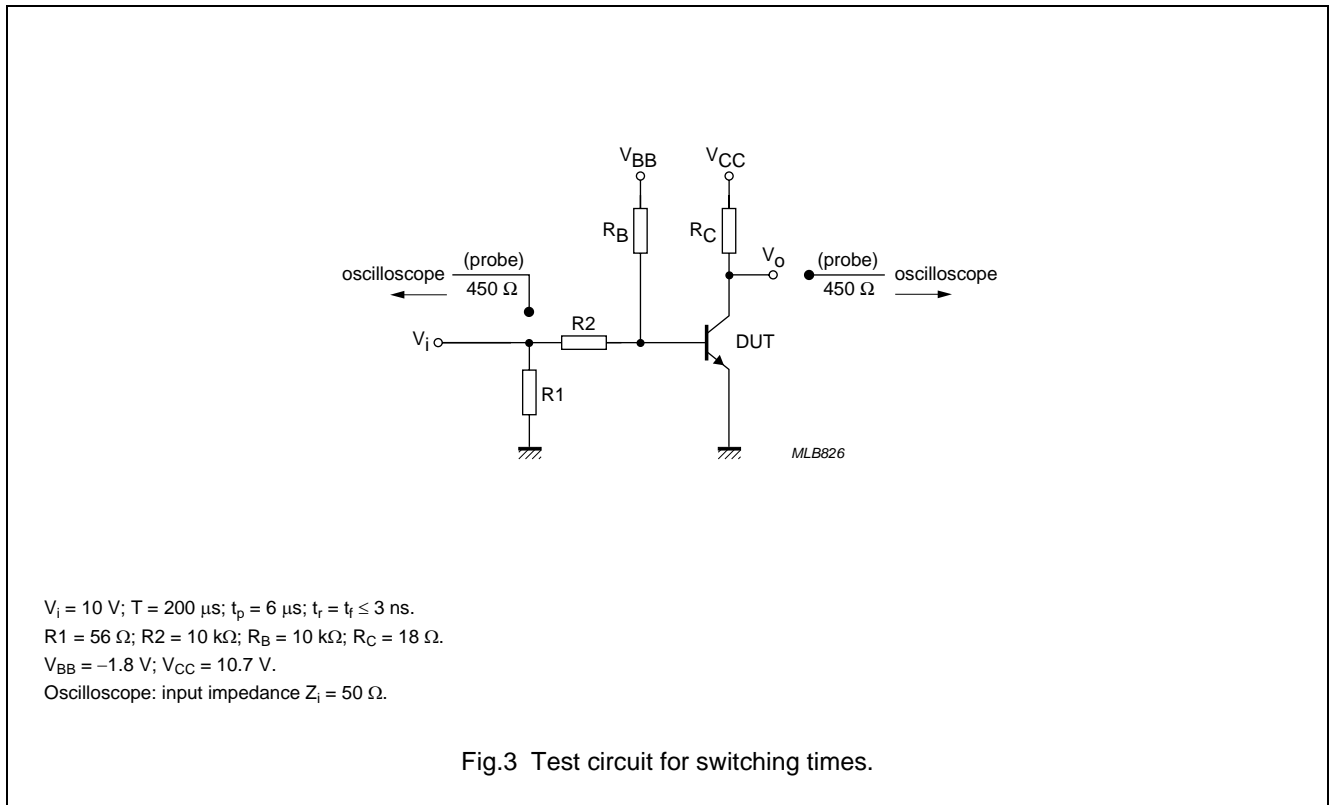
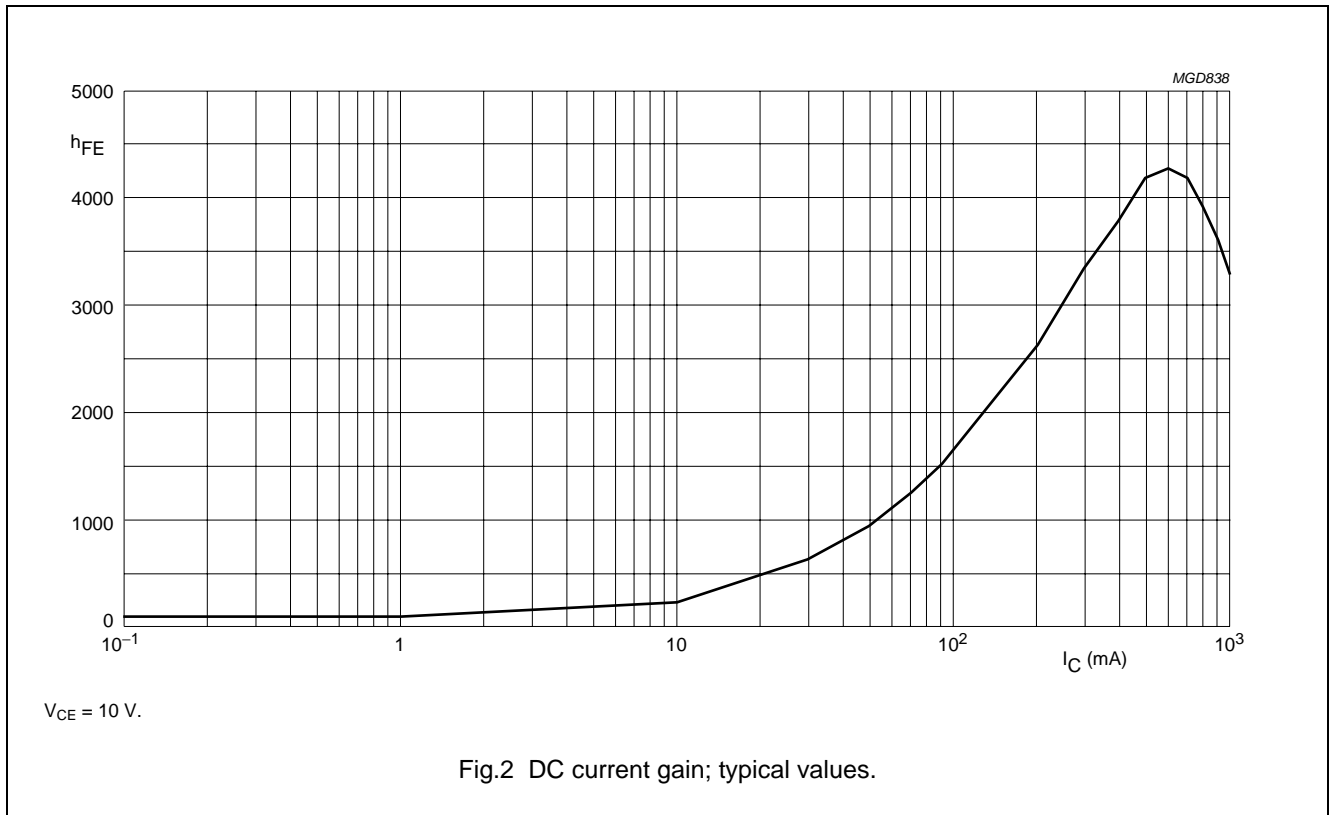
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CES}$	collector-emitter cut-off current					
	BST50	$V_{BE} = 0\text{ V}; V_{CE} = 45\text{ V}$	–	–	50	nA
	BST51	$V_{BE} = 0\text{ V}; V_{CE} = 60\text{ V}$	–	–	50	nA
	BST52	$V_{BE} = 0\text{ V}; V_{CE} = 80\text{ V}$	–	–	50	nA
$I_{EBO}$	emitter-base cut-off current	$I_C = 0\text{ A}; V_{EB} = 4\text{ V}$	–	–	50	nA
$h_{FE}$	DC current gain	$V_{CE} = 10\text{ V}$ ; note 1; (see Fig.2)				
		$I_C = 150\text{ mA}$	1000	–	–	
		$I_C = 500\text{ mA}$	2000	–	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 500\text{ mA}; I_B = 0.5\text{ mA}$	–	–	1.3	V
		$I_C = 500\text{ mA}; I_B = 0.5\text{ mA}; T_j = 150\text{ °C}$	–	–	1.3	V
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 500\text{ mA}; I_B = 0.5\text{ mA}$	–	–	1.9	V
$f_T$	transition frequency	$I_C = 500\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	–	200	–	MHz
<b>Switching times (between 10% and 90% levels); (see Fig.3)</b>						
$t_{on}$	turn-on time	$I_{Con} = 500\text{ mA}; I_{Bon} = 0.5\text{ mA}; I_{Boff} = -0.5\text{ mA}$	–	400	–	ns
$t_{off}$	turn-off time		–	1500	–	ns

**Note**

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

NPN Darlington transistors

BST50; BST51; BST52



NPN Darlington transistors

BST50; BST51; BST52

PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b <sub>p1</sub>	b <sub>p2</sub>	b <sub>p3</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT89		TO-243	SC-62		04-08-03 06-03-16

NPN Darlington transistors

BST50; BST51; BST52

**DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

**Notes**

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

**DISCLAIMERS**

**General** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

**Right to make changes** — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

**Suitability for use** — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

**Limiting values** — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions

above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

**Terms and conditions of sale** — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

# ***NXP Semiconductors***

## **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

## **Contact information**

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

© NXP B.V. 2009

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

R75/05/pp8

Date of release: 2004 Dec 09

Document order number: 9397 750 13877

founded by

**PHILIPS**



# Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[NXP:](#)

[BST50,115](#) [BST51,135](#) [BST51,115](#) [BST52,135](#) [BST52,115](#)